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Form 1449 (Modified) Information Disclosure Statement By Applicant <small>(Use Several Sheets if Necessary)</small>			Attorney Docket No: U.S. Lam2P466 Applicant: Lam Research Corporation Filing Date: 3/24/2004 Group: 1765
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U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class
<i>ALC4</i>	A	4,899,055	08/31/1990	Adams	250	372
	B	5,241,366	08/31/1993	Bevis et al.	356	382
	C	6,160,621	12/12/2000	Perry et al.	356	381
	D	6,556,947	04/30/2003	Scheiner et al.	702	172
✓	E	6,654,108	11/25/2003	Ravid et al.	356	237.2

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
<i>ALC4</i>	F	Harland G., Tompkins, <u>A User's Guide to Ellipsometry</u> , 1993, Academic Press, Inc., New York, pg.253-255
	G	Dag et al., "Performing STI process control using large-spot-size Fourier-transform reflectometry" April 2003, MicroMagazine , pgs.25-30
	H	Ouma et al., "Characterization and Modeling of Oxide- Chemical - Mechanical Polishing Using Planarization Length and Pattern Density Concepts" May 2002, IEEE Transactions on Semiconductor Manufacturing Vol 15 No.2 pp 232 - 244 .
	I	DeJule, Ruth "Advances in Thin Film Measurement" May 1, 1998 Semiconductor Intl.
✓	J	Tevet, In-Situ Thickness Monitoring System, Aug 2001 http://www.tevet-pct.com/docs/apcPoster.pdf
Examiner		Date Considered
<i>greta glenn</i>		<i>9/29/05</i>

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Form 1449 (Modified)

Information Disclosure Statement By Applicant

(Use Several Sheets if Necessary)

Attorney Docket No:	U.S.
LAM2P466	10/810,209
Applicant:	
Y. Gotkis	
Filing Date:	Group:
March 26, 2004	1765

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class
AGC	A	US 2002/0054290 A1	05/2002	Vurens et al.	356	369
↓	B	5,898,181	04/1999	Vurens	250	559.28
C						
D						
E						
F						
G						
H						
I						

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
AGC	J	2000028748 A Patent Abstracts of Japan	28/01/00 Jan. 28, 2000	EPO JP	G01V	8/12		X
↓	K	WO 00/12958	09/03/00	WIPO	G01B	9/02		X
	L	0 296 365 A1	28/12/88	EPO	G01T	1/29		X
↓	M	WO 99/08066	18/02/99	WIPO	G01B	9/02		X
	N							

Other Documents

Examiner		
Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	O	
	P	
Examiner		Date Considered
↓ Rita K. Blanks		9/29/05

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.